

Technical Data Sheet

Opto Interrupter SGM9809

■ Features

- Fast response time
- High analytic
- Peak wavelength $\lambda_p=940\text{nm}$
- High sensitivity
- Pb free



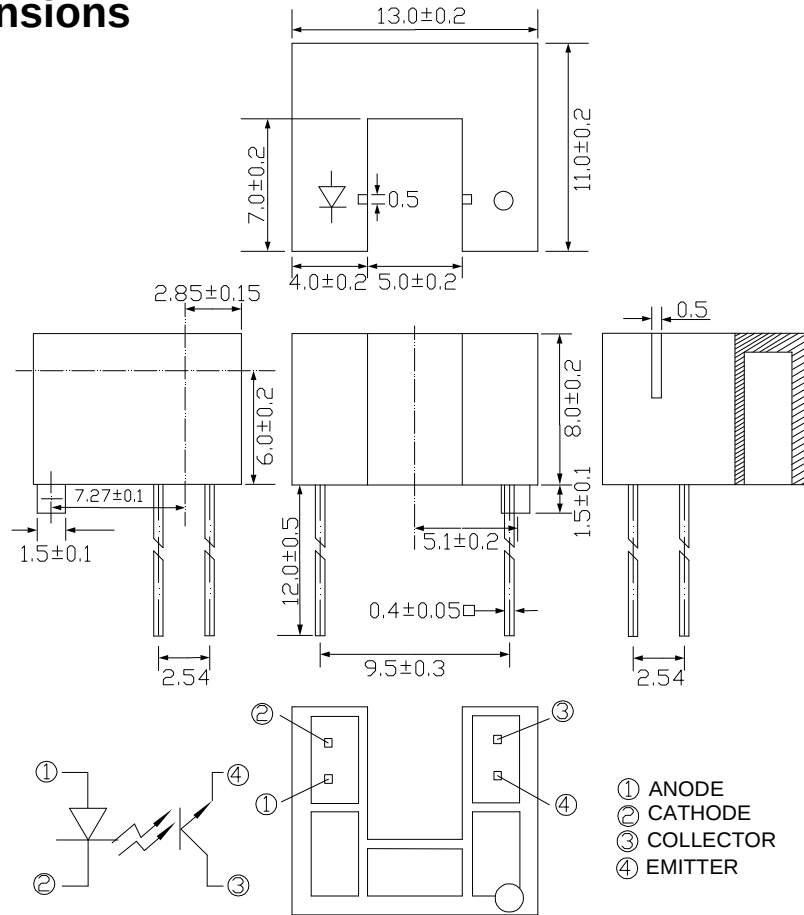
■ Descriptions

The SGM9809 consist of an infrared emitting diode and an NPN silicon phototransistor, encased side-by-side on converging optical axis in a black thermoplastic housing . The phototransistor receives radiation from the IR LED only. This is the normal situation. But when an object is in between , phototransistor could not receives the radiation.

■ Applications

- Non-contact Switching
- Switch Scanner
- For Direct Board
- Floppy disk driver

Package Dimensions



Note: 1. All dimensions are in millimeters
2. Tolerances unless dimensions $\pm 0.3\text{mm}$

Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Parameter		Symbol	Rating	Units
Input	Power Dissipation at(or below) 25°C Free Air Temperature	P_d	75	mW
	Reverse Voltage	V_R	5	V
	Continuous Forward Current	I_F	50	mA
	Peak Forward Current (*1)	I_{FP}	0.5	A
Output	Collector Power Dissipation	P_d	75	mW
	Collector Current	I_c	20	mA
	Collector-Emitter Voltage	V_{CEO}	30	V
	Emitter-Collector-Voltage	V_{ECO}	5	V
Lead Soldering Temperature (*2)		T_{sol}	260	°C
Operating Temperature		T_{opr}	-25 ~ +85	°C
Storage Temperature		T_{stg}	-40 ~ +85	°C

Notes: *1: I_{FP} Conditions--Pulse Width $\leq 100 \mu s$ and Duty $\leq 1\%$.

*2:Soldering time ≤ 5 seconds.

■ Electro-Optical Characteristics (Ta=25°C)

Parameter		Symbol	Min.	Typ.	Max.	Units	Conditions
Input	Forward Voltage	V_F	--	1.2	1.5	V	$I_F = 20\text{mA}$
	Reverse Current	I_R	--	--	10	μA	$V_R = 5\text{V}$
	Peak Wavelength	λ_p	--	940	--	nm	$I_F = 20\text{mA}$
	View Angle	$2\theta_{1/2}$	--	60	--	Deg	$I_F = 20\text{mA}$
Output	Dark Current	I_{CEO}	--	--	100	nA	$V_{CE} = 20\text{V}$, $E_e = 0\text{mw/cm}^2$
	C-E Saturation Voltage	$V_{CE(S)}$	-	--	0.4	V	$I_C = 2\text{mA}$, $E_e = 1\text{mw/cm}^2$
Transfer Characteristics	Collector Current	$I_C(ON)$	0.5	--	10	mA	$V_{CE} = 5\text{V}$, $I_F = 20\text{mA}$
		$I_C(OFF)$	--	--	20	μA	
	Rise Time	t_r	--	15		μs	$V_{CE} = 5\text{V}$, $I_C = 1\text{mA}$
	Fall Time	t_f	--	15		μs	$R_L = 1000$

■ Typical Electro-Optical Characteristics Curves for IR

Fig.1 Forward Current vs.
Ambient Temperature

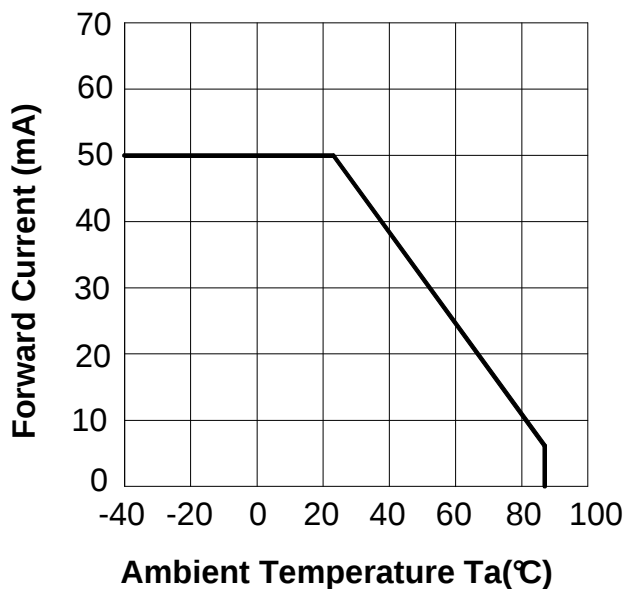


Fig.2 Spectral Distribution

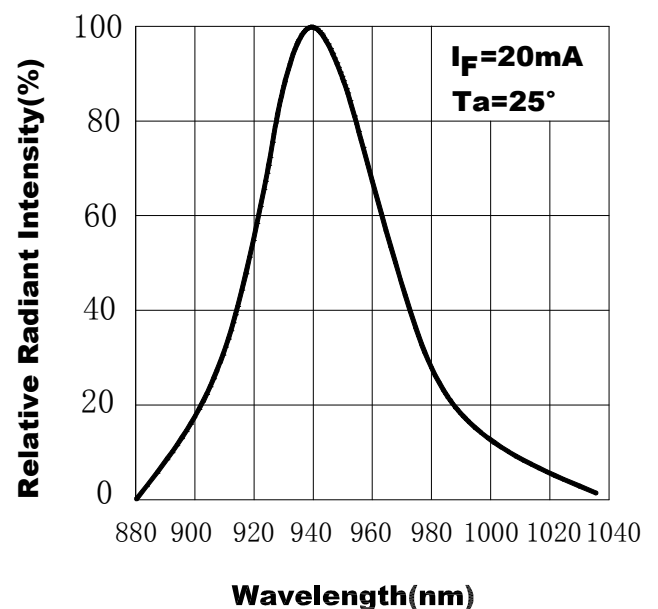


Fig.3 Peak Emission Wavelength vs.
Ambient Temperature

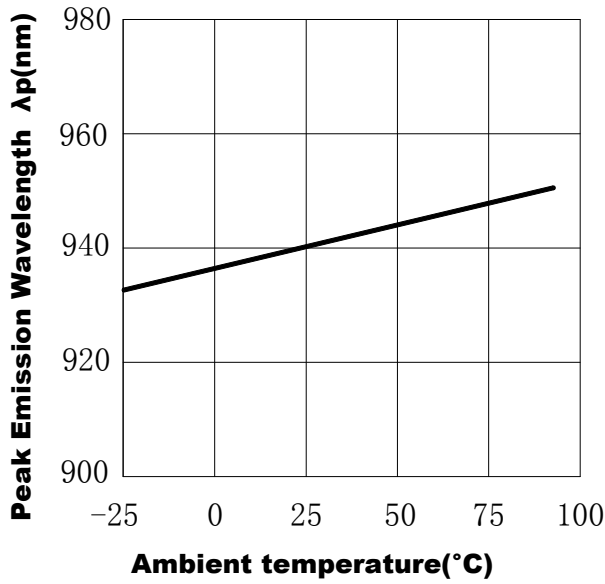


Fig.4 Forward Current vs.
Forward Voltage

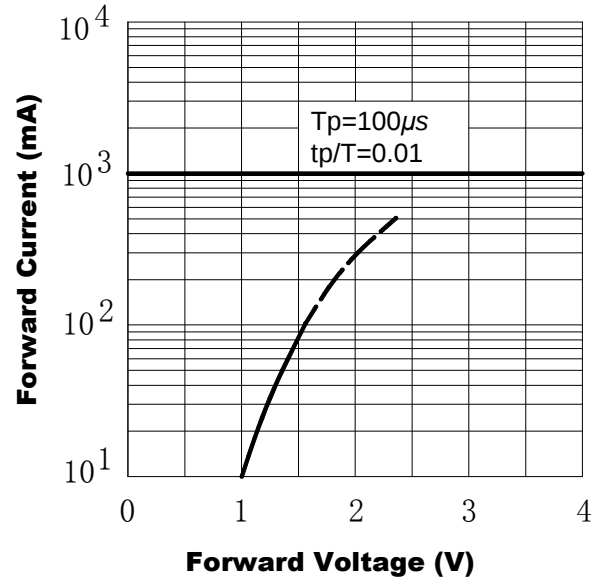


Fig.5 Radiant Intensity vs.
Forward Current

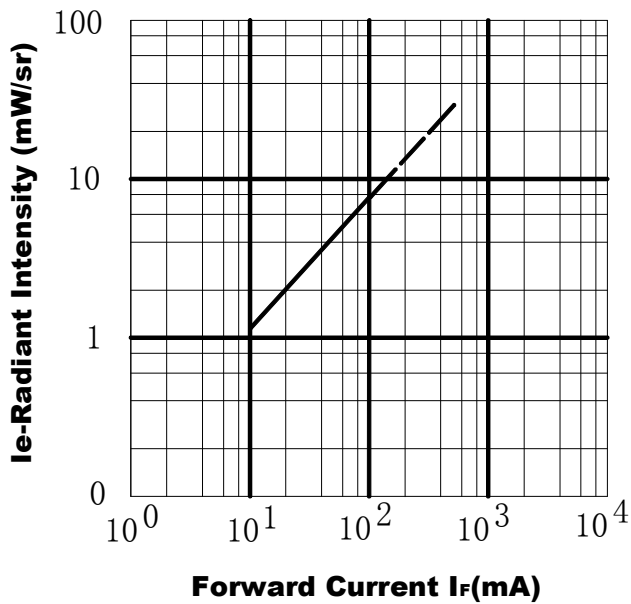
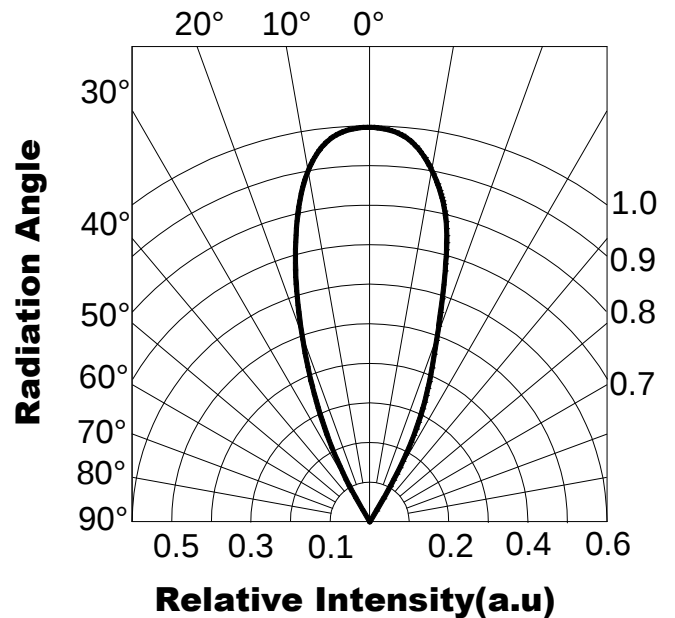


Fig.6 Relative Radiant Intensity vs.
Angular Displacement



■ Typical Electro-Optical Characteristics Curves for PT

Fig.1 Collector Power Dissipation vs. Ambient Temperature

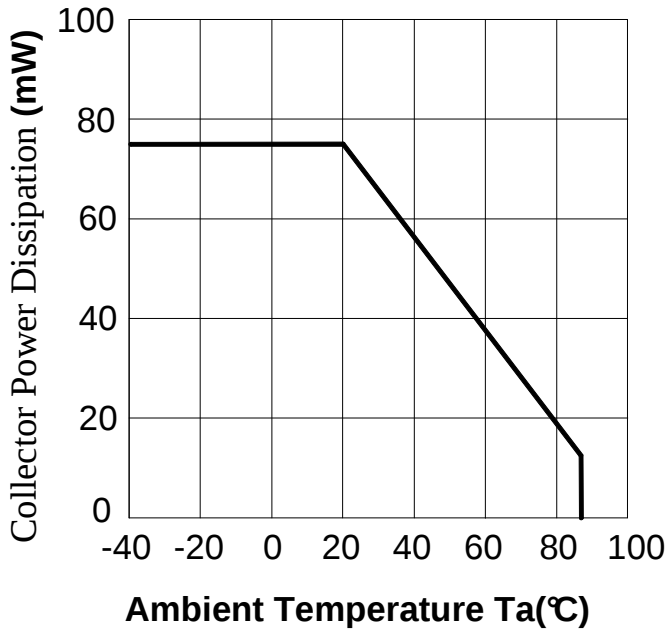


Fig.2 Spectral Sensitivity

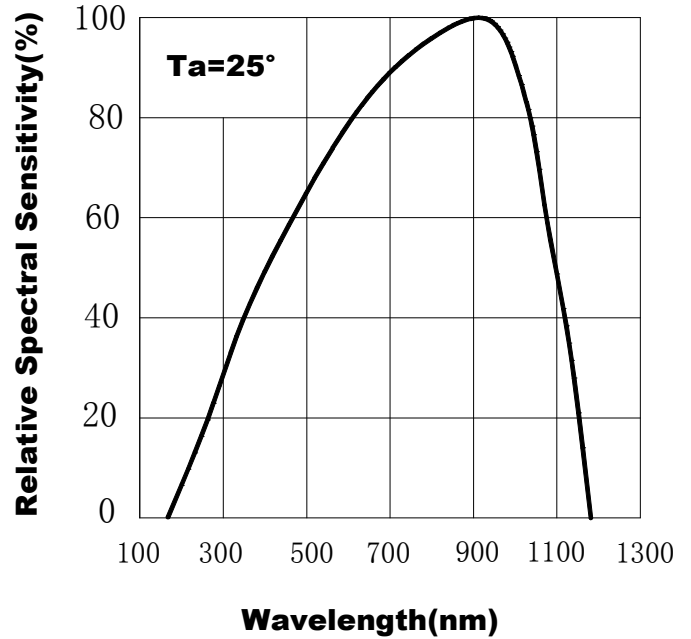


Fig.3 Relative Collector Current vs. Ambient Temperature

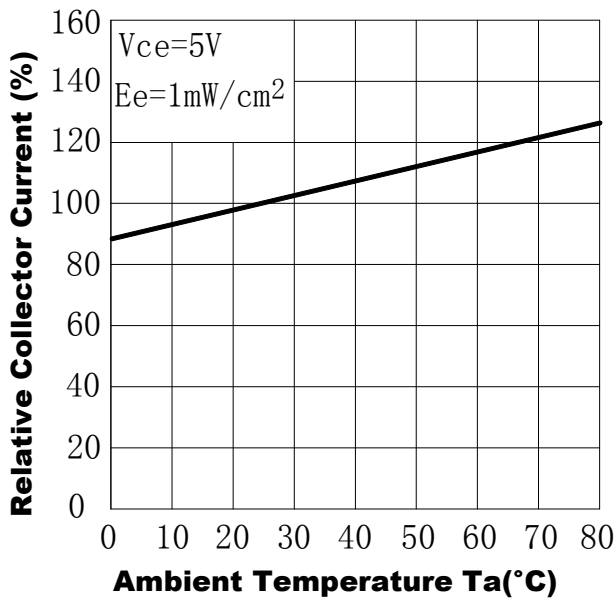


Fig.4 Collector Current vs. Irradiance

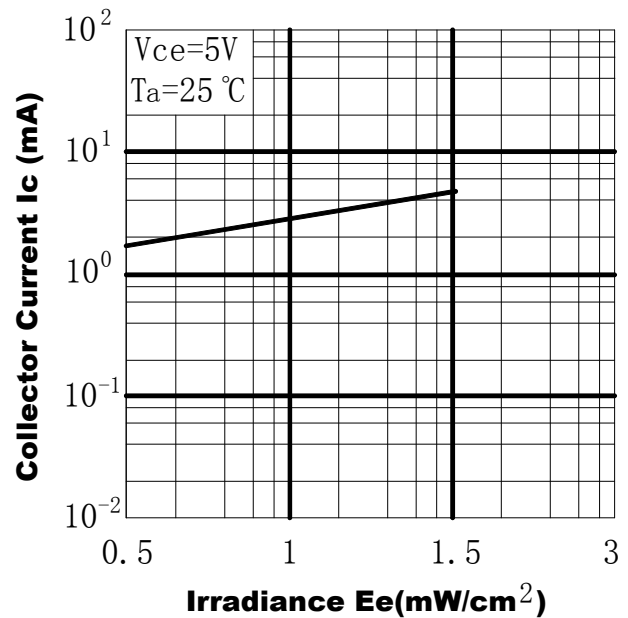


Fig.5 Collector Dark Current vs.
Ambient Temperature

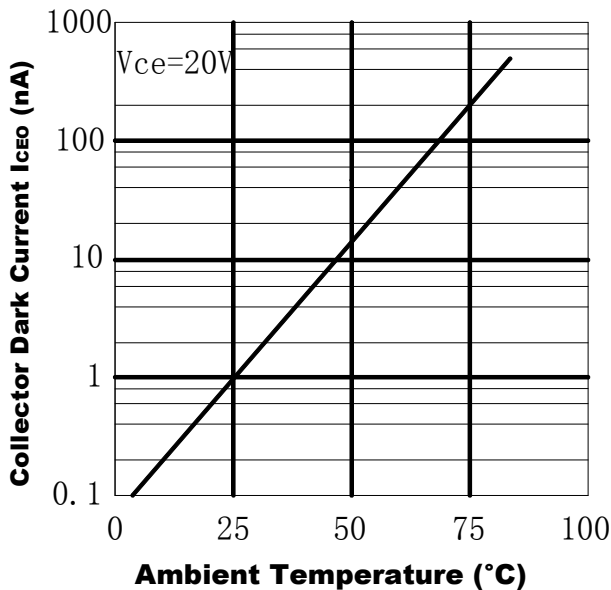
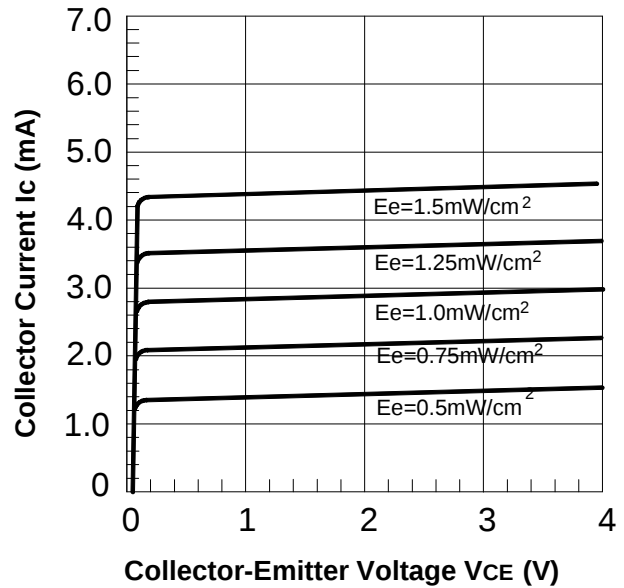


Fig.6 Collector Current vs.
Collector-Emitter Voltage



■ Packing Quantity Specification

1. 100PCS/1Bag

■ Notes

1. Above specification may be changed without notice. SHUGUAN will reserve authority on material change for above specification.
2. When using this product, please observe the absolute maximum ratings and the instructions for using outlined in these specification sheets. SHUGUAN assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
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